

2SD1771, 2SD1771A

Silicon NPN triple diffusion planar type

For power amplification

For TV vertical deflection output

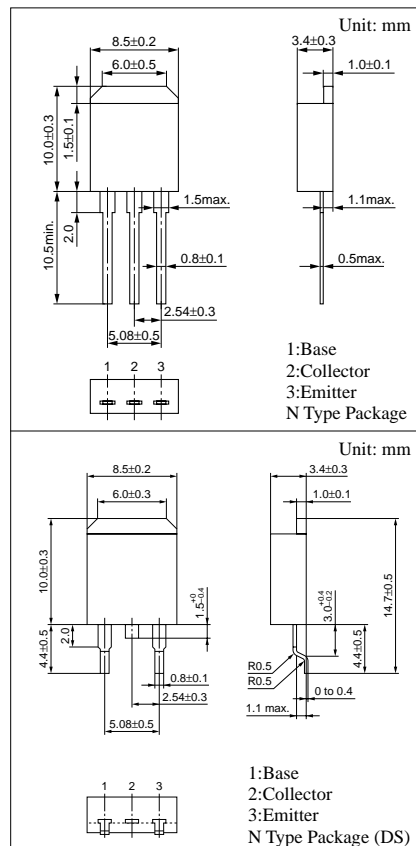
Complementary to 2SB1191 and 2SB1191A

Features

- High collector to emitter V_{CEO}
- Large collector power dissipation P_C
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Rated	Unit
Collector to base voltage	V_{CB0}	200	V
Collector to emitter voltage	V_{CEO}	150	V
		180	V
Emitter to base voltage	V_{EBO}	6	V
Peak collector current	I_{CP}	2	A
Collector current	I_C	1	A
Collector power dissipation	P_C	25	W
		1.3	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



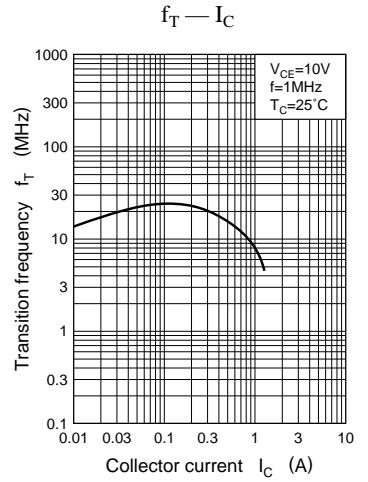
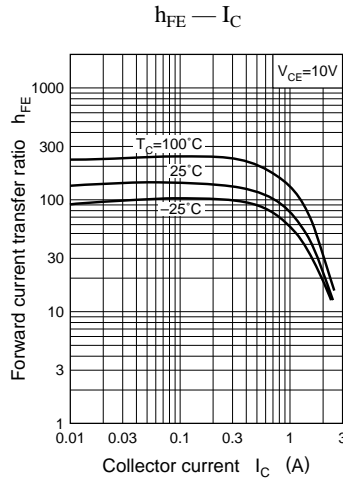
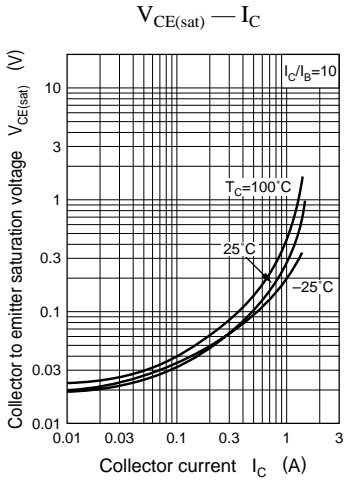
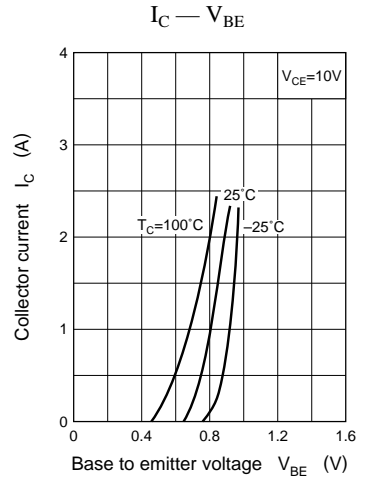
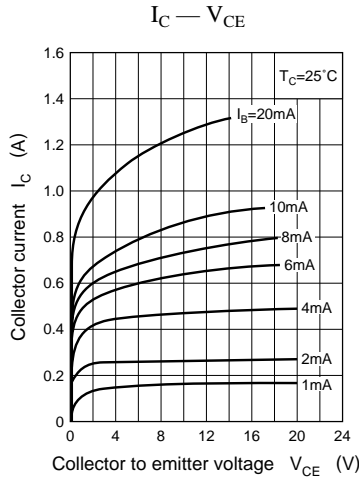
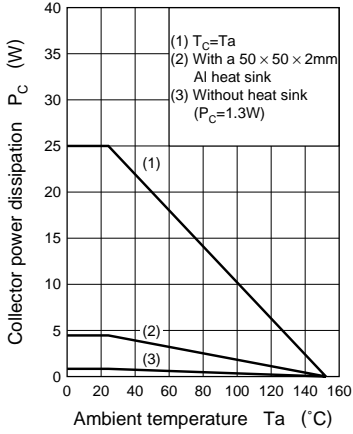
Electrical Characteristics ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CB0}	$V_{CB} = 200\text{V}, I_E = 0$			50	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$			50	μA
Collector to emitter voltage	V_{CEO}	$I_C = 5\text{mA}, I_B = 0$	150			V
			180			V
Emitter to base voltage	V_{EBO}	$I_E = 0.5\text{mA}, I_C = 0$	6			V
Forward current transfer ratio	h_{FE1}^*	$V_{CE} = 10\text{V}, I_C = 100\text{mA}$	60		240	
	h_{FE2}	$V_{CE} = 10\text{V}, I_C = 300\text{mA}$	50			
Base to emitter voltage	V_{BE}	$V_{CE} = 10\text{V}, I_C = 300\text{mA}$			1	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			1	V
Transition frequency	f_T	$V_{CE} = 10\text{V}, I_C = 100\text{mA}, f = 1\text{MHz}$		20		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		27		pF

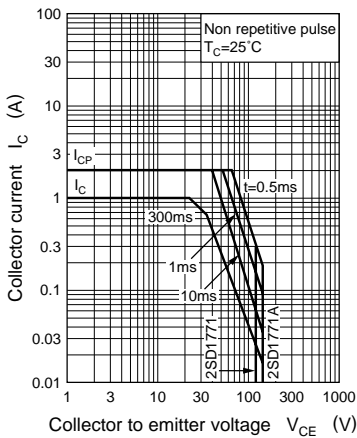
* h_{FE1} Rank classification

Rank	Q	P
h_{FE1}	60 to 140	100 to 240

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Area of safe operation (ASO)



$R_{th(t)} - t$

